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List of Publications by Year
in descending order

45 papers	1,557 citations	361413 20 h-index	477307 29 g-index
45 all docs	45 docs citations	45 times ranked	576 citing authors

#	ARTICLE	IF	CITATIONS
1	Selective surface migration for defect-free quantum dot ensembles using metal organic chemical vapor deposition. Journal of Crystal Growth, 2003, 255, 213-219.	1.5	15
2	Ultrafast carrier dynamics in size-controlled, self-assembled, InGaAs/GaAs quantum dots. , 2001, , .		0
3	Low-threshold oxide-confined 1.3-Î¼m quantum-dot laser. IEEE Photonics Technology Letters, 2000, 12, 230-232.	2.5	264
4	Very low threshold oxide-confined 1.3 /spl mu/m GaAs-based quantum dot laser. , 2000, , .		0
5	Continuous-wave low-threshold performance of 1.3-/spl mu/m InGaAs-GaAs quantum-dot lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 452-461.	2.9	55
6	Ultralow-threshold cryogenic vertical-cavity surface-emitting laser. IEEE Photonics Technology Letters, 2000, 12, 1-3.	2.5	19
7	Low-threshold continuous-wave two-stack quantum-dot laser with reduced temperature sensitivity. IEEE Photonics Technology Letters, 2000, 12, 1120-1122.	2.5	51
8	Toward quantum entanglement in a quantum-dot nanocavity. , 1999, , .		0
9	Spontaneous emission and threshold characteristics of 1.3-Î¼m InGaAs-GaAs quantum-dot GaAs-based lasers. IEEE Journal of Quantum Electronics, 1999, 35, 1238-1246.	1.9	85
10	Enhanced spontaneous emission using quantum dots and an apertured microcavity. IEEE Journal of Quantum Electronics, 1999, 35, 1502-1508.	1.9	31
11	Temperature dependence of lasing characteristics for long-wavelength (1.3-Î¼m) GaAs-based quantum-dot lasers. IEEE Photonics Technology Letters, 1999, 11, 301-303.	2.5	123
12	Intracavity contacts for low-threshold oxide-confined vertical-cavity surface-emitting lasers. IEEE Photonics Technology Letters, 1999, 11, 934-936.	2.5	49
13	Cavity-induced antiguiding in a selectively oxidized vertical-cavity surface-emitting laser. IEEE Photonics Technology Letters, 1998, 10, 12-14.	2.5	44
14	1.15-Î¼m wavelength oxide-confined quantum-dot vertical-cavity surface-emitting laser. IEEE Photonics Technology Letters, 1998, 10, 185-187.	2.5	77
15	Mode coupling in a narrow spectral bandwidth quantum-dot microcavity photodetector. IEEE Photonics Technology Letters, 1998, 10, 252-254.	2.5	5
16	Threshold temperature dependence of lateral-cavity quantum-dot lasers. IEEE Photonics Technology Letters, 1998, 10, 1673-1675.	2.5	23
17	Hybrid dielectric/metal reflector for low threshold vertical-cavity surface-emitting lasers. Electronics Letters, 1997, 33, 1704.	1.0	8
18	Low-threshold continuous-wave operation of an oxide-confined vertical cavity surface emitting laser based on a quantum dot active region and half-wave cavity. Electronics Letters, 1997, 33, 1225.	1.0	20

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19	Mode confinement in the ultralow threshold Fabry-Perot microcavity laser. , 1997, , .		0
20	Eigenmode confinement in the dielectrically apertured Fabry-Perot microcavity [VCSEL]. IEEE Photonics Technology Letters, 1997, 9, 713-715.	2.5	36
21	Tunnel injection active region in an oxide-confined vertical-cavity surface-emitting laser. IEEE Photonics Technology Letters, 1997, 9, 716-718.	2.5	5
22	Low-threshold proton-implanted 1.3-Î¼m vertical-cavity top-surface-emitting lasers with dielectric and wafer-bonded GaAs-AlAs Bragg mirrors. IEEE Photonics Technology Letters, 1997, 9, 866-868.	2.5	16
23	Comparison of vertical-cavity surface-emitting lasers with half-wave cavity spacers confined by single- or double-oxide apertures. IEEE Photonics Technology Letters, 1997, 9, 875-877.	2.5	22
24	Low-threshold vertical-cavity surface-emitting lasers based on oxide-confinement and high contrast distributed Bragg reflectors. IEEE Journal of Selected Topics in Quantum Electronics, 1997, 3, 893-904.	2.9	66
25	Fabrication of high-packing-density vertical cavity surface-emitting laser arrays using selective oxidation. IEEE Photonics Technology Letters, 1996, 8, 596-598.	2.5	16
26	Multiwavelength, densely-packed 2 x 2 vertical-cavity surface-emitting laser array fabricated using selective oxidation. IEEE Photonics Technology Letters, 1996, 8, 858-860.	2.5	48
27	Sub-40 Î¼A continuous-wave lasing in an oxidized vertical-cavity surface-emitting laser with dielectric mirrors. IEEE Photonics Technology Letters, 1996, 8, 974-976.	2.5	101
28	Very-low-threshold index-confined planar microcavity lasers. IEEE Photonics Technology Letters, 1995, 7, 965-967.	2.5	57
29	Transverse and temporal mode dependence on mirror contrast in microcavity lasers. IEEE Journal of Quantum Electronics, 1995, 31, 2026-2036.	1.9	11
30	Low threshold half-wave vertical-cavity lasers. Electronics Letters, 1994, 30, 1946-1947.	1.0	121
31	Mode dependence on mirror contrast in Fabry-Perot microcavity lasers. IEEE Photonics Technology Letters, 1994, 6, 135-138.	2.5	20
32	Low-threshold continuous-wave surface emitting lasers with etched void confinement. IEEE Photonics Technology Letters, 1994, 6, 320-322.	2.5	37
33	Spontaneous Emission from Planar Microstructures. Journal of Modern Optics, 1994, 41, 325-344.	1.3	126
34	Low threshold vertical-cavity lasers based on native-oxidation of alas. , 0, , .		1
35	Oxide-confined VCSELs with quantum well and quantum dot active regions. , 0, , .		3
36	Wavelength control through lateral device size in a 2Ã—2 vertical-cavity surface-emitting laser array fabricated using selective oxidation. , 0, , .		0

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37	Dosage effects on oxygen implanted single-bonded 1.3 Î¼m vertical-cavity surface-emitting lasers. , 0, , .		0
38	1.27 Î¼m resonant cavity PIN photodetector using an InAs/GaAs quantum dot active region grown on GaAs. , 0, , .		0
39	Low threshold Al/sub x/O/sub y/-confined VCSELs and densely-packed arrays. , 0, , .		0
40	Oxide-apertured VCSELS with use of oxide/GaAs distributed Bragg reflectors and tunnel injection. , 0, , .		0
41	Low-threshold continuous-wave operation of an oxide-confined vertical-cavity surface-emitting laser based on a quantum dot active region and half-wave cavity. , 0, , .		0
42	Single-mode vertical-cavity surface-emitting laser with cavity induced antiguiding. , 0, , .		0
43	Dielectric apertures for mode control in low threshold and single mode vertical-cavity surface-emitting lasers. , 0, , .		0
44	Purcell effect and the bias-free pulse response of vertical-cavity surface-emitting lasers. , 0, , .		0
45	1.3 Î¼m quantum dot lasers with single and stacked active layers. , 0, , .		2